

BLF184XR; BLF184XRS

Power LDMOS transistor

Rev. 3 — 1 April 2014

Product data sheet

1. Product profile

1.1 General description

A 700 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η _D (%)
pulsed RF	108	50	700	23.9	73.5
CW	108	50	750	23.5	81.9

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

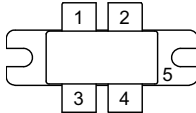
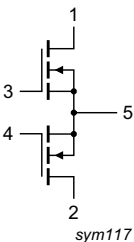
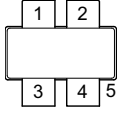
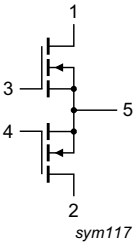
1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF184XR (SOT1214A)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source [1]		
BLF184XRS (SOT1214B)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF184XR	-	flanged ceramic package; 2 mounting holes; 4 leads	SOT1214A
BLF184XRS	-	earless flanged ceramic package; 4 leads	SOT1214B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	V
V_{GS}	gate-source voltage		-6	+11	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature	[1]	-	225	°C

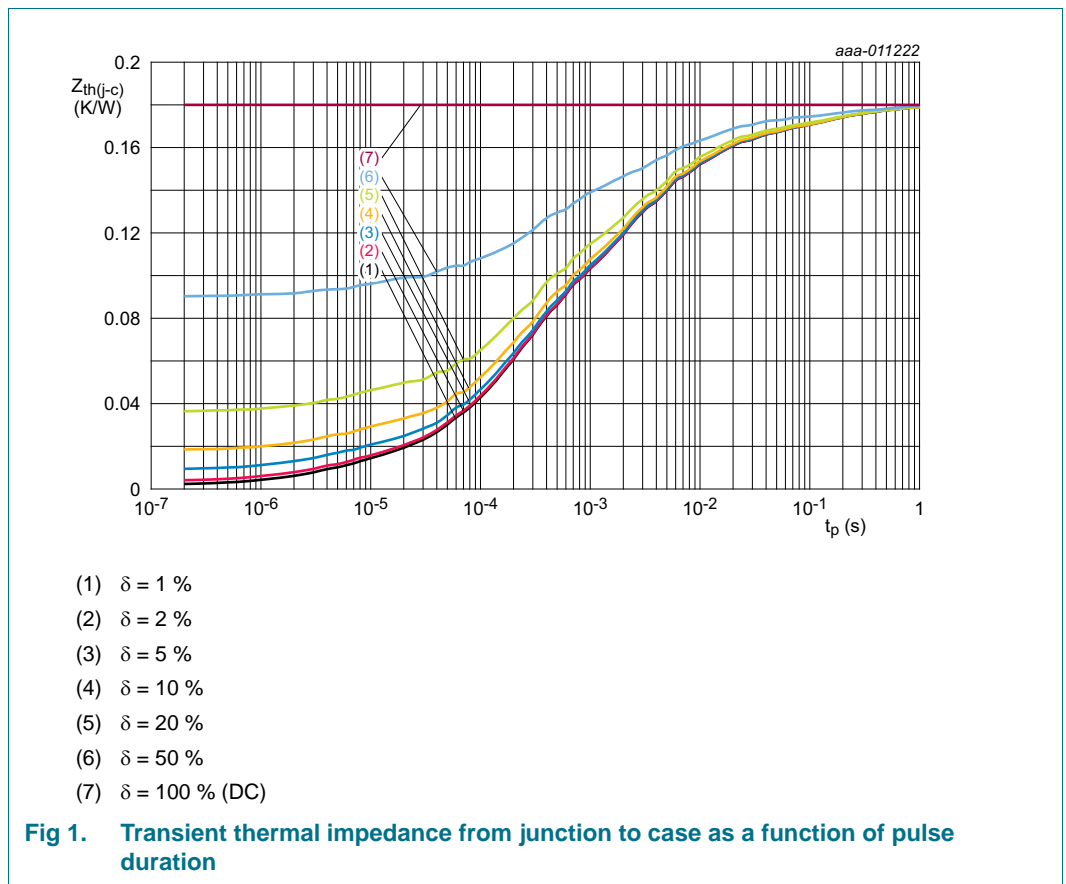
[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_j = 150\text{ °C}$ [1][2]	0.18	K/W
$Z_{th(j-c)}$	transient thermal impedance from junction to case	$T_j = 150\text{ °C}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\text{ %}$ [3]	0.065	K/W

- [1] T_j is the junction temperature.
- [2] $R_{th(j-c)}$ is measured under RF conditions.
- [3] See [Figure 3](#).



6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ °C}$; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 2.75\text{ mA}$	135	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 275\text{ mA}$	1.25	1.9	2.25	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50\text{ V}$; $I_D = 50\text{ mA}$	-	1.6	-	V

Table 6. DC characteristics ...continued
 $T_j = 25\text{ }^\circ\text{C}$; per section unless otherwise specified.

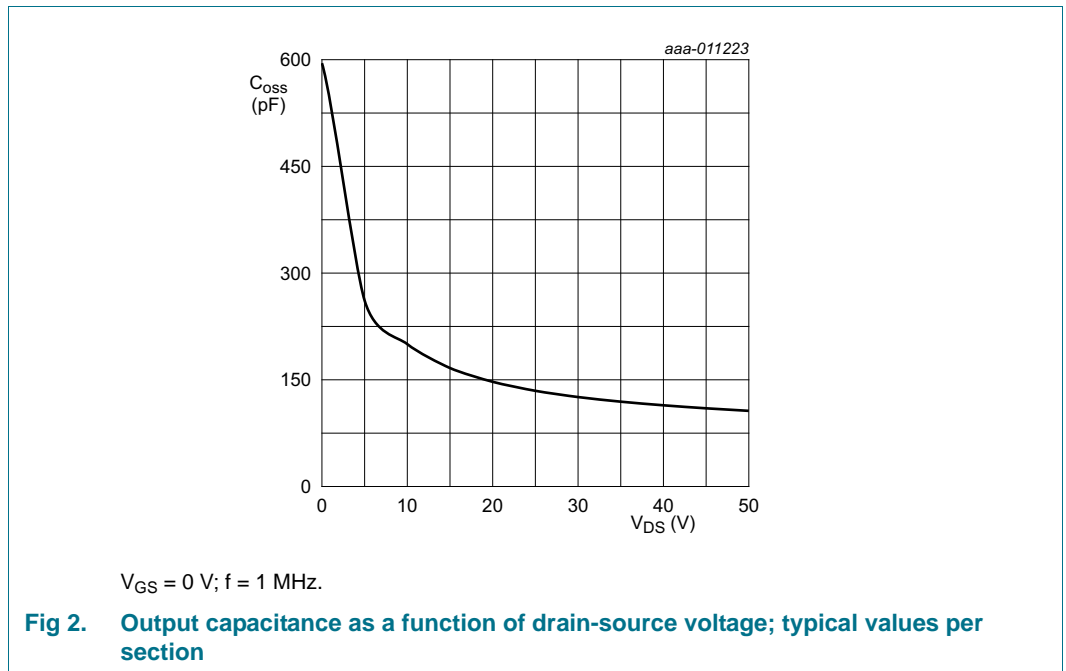
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}$	-	-	1.4	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; V_{DS} = 10\text{ V}$	-	38.5	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; I_D = 9.625\text{ A}$	-	0.16	-	Ω

Table 7. AC characteristics
 $T_j = 25\text{ }^\circ\text{C}$; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	3.1	-	pF
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	292	-	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	107	-	pF

Table 8. RF characteristics
 Test signal: pulsed RF; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\%$; $f = 108\text{ MHz}$; RF performance at $V_{DS} = 50\text{ V}$; $I_{Dq} = 100\text{ mA}$; $T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_L = 700\text{ W}$	22.8	23.9	-	dB
RL_{in}	input return loss	$P_L = 700\text{ W}$	-	-20	-13	dB
η_D	drain efficiency	$P_L = 700\text{ W}$	71	73.5	-	%



7. Test information

7.1 Ruggedness in class-AB operation

The BLF184XR and BLF184XRS are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: $V_{DS} = 50\text{ V}$; $I_{DQ} = 100\text{ mA}$; $P_L = 700\text{ W}$ pulsed; $f = 108\text{ MHz}$.

7.2 Impedance information

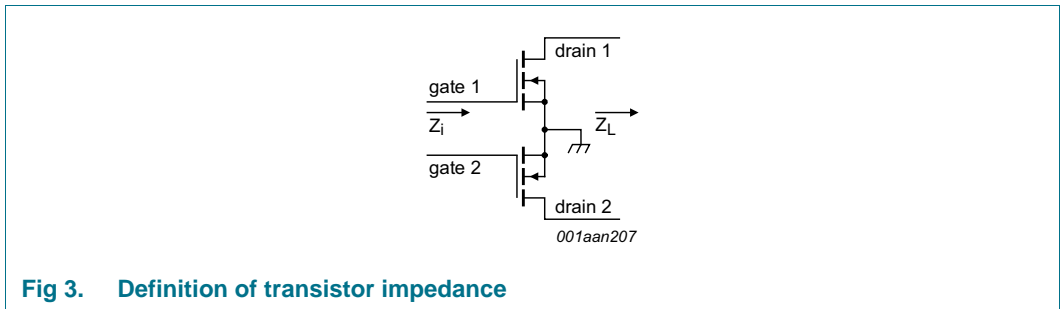


Fig 3. Definition of transistor impedance

Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50\text{ V}$ and $P_L = 700\text{ W}$.

f	Z_i	Z_L
(MHz)	(Ω)	(Ω)
108	$5.8 - j19.1$	$5.5 + j1.0$

7.3 UIS avalanche energy

Table 10. Typical avalanche data per section

$T_{amb} = 25\text{ }^\circ\text{C}$; typical test data; test jig without water cooling.

I_{AS}	E_{AS}
(A)	(J)
15	4.3
20	2.1
25	1.3

For information see application note AN10273.

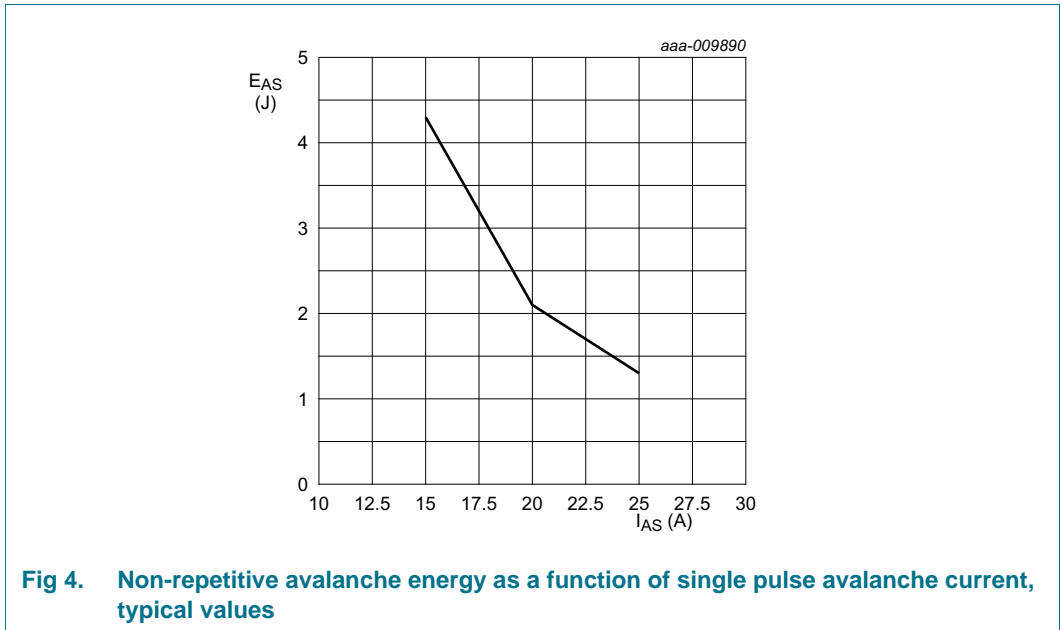


Fig 4. Non-repetitive avalanche energy as a function of single pulse avalanche current, typical values

7.4 Test circuit

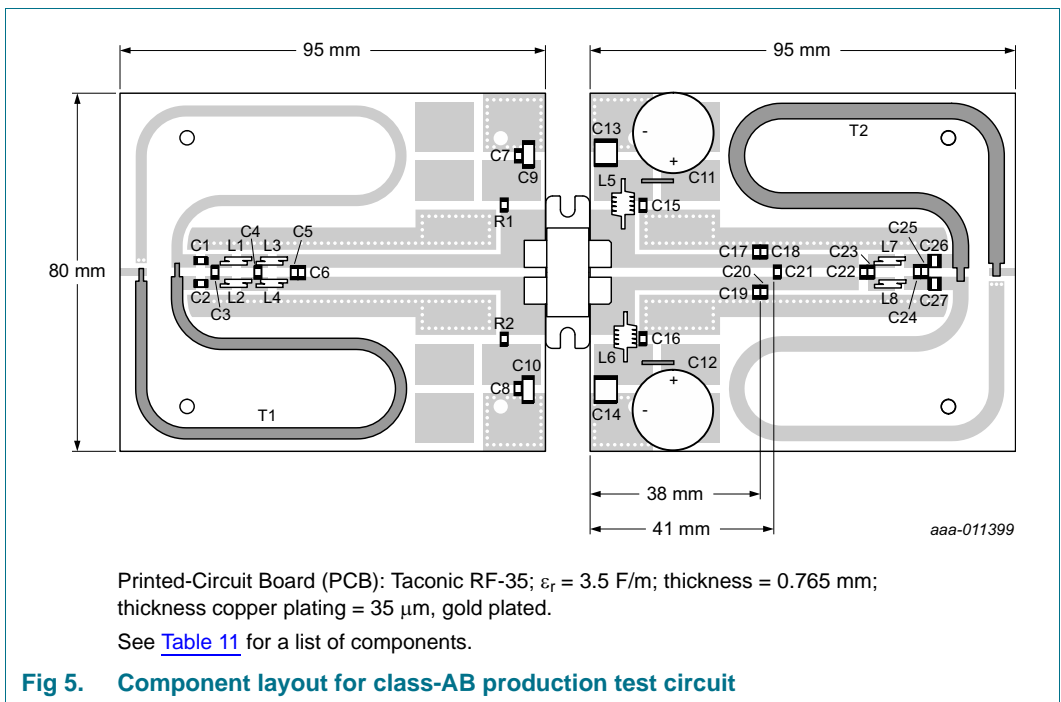


Fig 5. Component layout for class-AB production test circuit

Table 11. List of components

For test circuit see [Figure 5](#).

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	910 pF	[1]
C3	multilayer ceramic chip capacitor	47 pF	[1]
C4	multilayer ceramic chip capacitor	51 pF	[1]

Table 11. List of components ...continuedFor test circuit see [Figure 5](#).

Component	Description	Value	Remarks
C5	multilayer ceramic chip capacitor	100 pF	[1]
C6, C23	multilayer ceramic chip capacitor	20 pF	
C7, C8, C15, C16	multilayer ceramic chip capacitor	820 pF	[1]
C9, C10, C13, C14	multilayer ceramic chip capacitor	4.7 μ F, 100 V	TDK C5750X7R2A475KT
C11, C12	electrolytic capacitor	1000 μ F, 63 V	
C17, C19	multilayer ceramic chip capacitor	39 pF	[1]
C18, C20	multilayer ceramic chip capacitor	27 pF	[1]
C21	multilayer ceramic chip capacitor	7.5 pF	[1]
C22	multilayer ceramic chip capacitor	22 pF	[1]
C24, C25	multilayer ceramic chip capacitor	27 pF	[1]
C26, C27	multilayer ceramic chip capacitor	1 nF	[2]
L1, L2, L3, L4	1.5 turn 0.8 mm copper wire	D = 2.8 mm	
L5, L6	5.5 turn 0.8 mm copper wire	D = 3.6 mm	
L7, L8	1 turn 1.5 mm copper wire	D = 4 mm	
R1, R2	resistor	10 Ω	SMD 1206
T1	semi rigid coax	25 Ω , length = 160 mm	Micro-Coax UT-090C-25
T2	semi rigid coax	25 Ω , length = 160 mm	Micro-Coax UT-141C-25

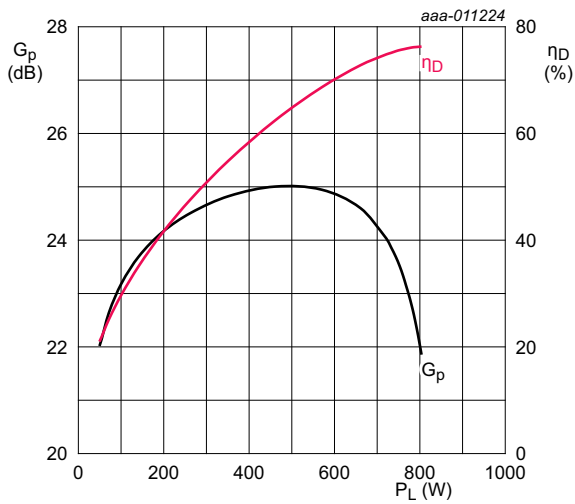
[1] American Technical Ceramics type 800B or capacitor of same quality.

[2] American Technical Ceramics type 100B or capacitor of same quality.

7.5 Graphical data

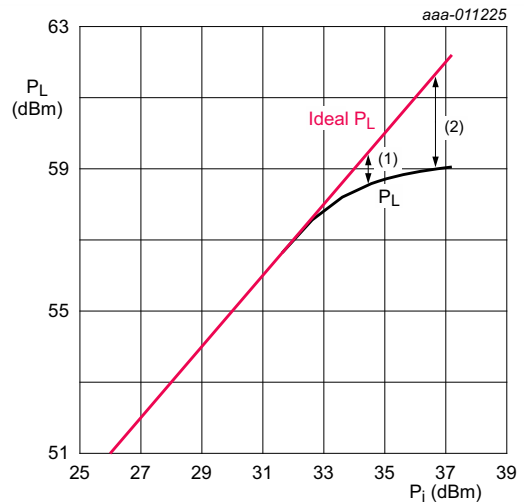
The following figures are measured in a class-AB production test circuit.

7.5.1 1-Tone CW pulsed



$V_{DS} = 50\text{ V}; I_{Dq} = 100\text{ mA}; f = 108\text{ MHz}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ \%}$.

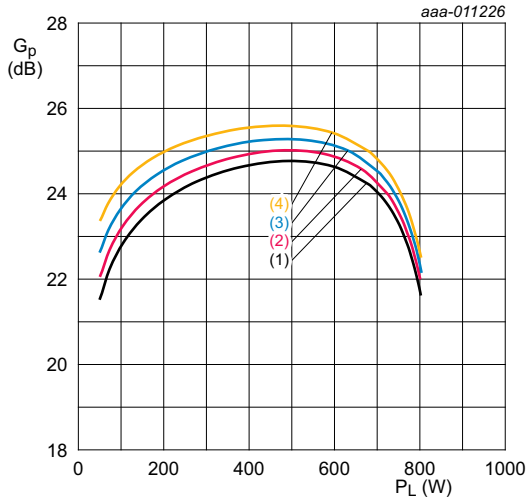
Fig 6. Power gain and drain efficiency as function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 100\text{ mA}; f = 108\text{ MHz}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ \%}$.

- (1) $P_{L(1dB)} = 58.6\text{ dBm (720 W)}$
- (2) $P_{L(3dB)} = 59\text{ dBm (800 W)}$

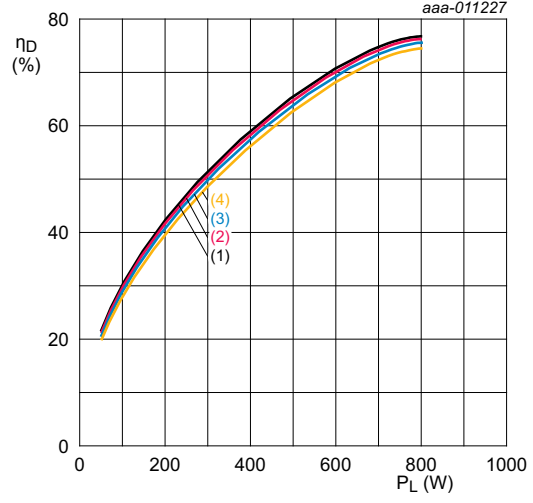
Fig 7. Output power as a function of input power; typical values



$V_{DS} = 50\text{ V}$; $f = 108\text{ MHz}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\text{ }\%$.

- (1) $I_{Dq} = 50\text{ mA}$
- (2) $I_{Dq} = 100\text{ mA}$
- (3) $I_{Dq} = 200\text{ mA}$
- (4) $I_{Dq} = 400\text{ mA}$

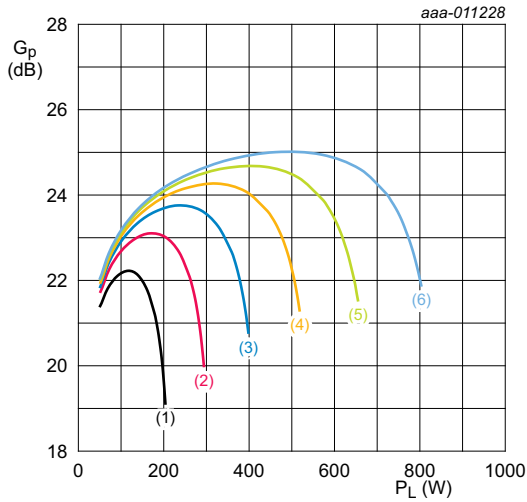
Fig 8. Power gain as a function of output power; typical values



$V_{DS} = 50\text{ V}$; $f = 108\text{ MHz}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\text{ }\%$.

- (1) $I_{Dq} = 50\text{ mA}$
- (2) $I_{Dq} = 100\text{ mA}$
- (3) $I_{Dq} = 200\text{ mA}$
- (4) $I_{Dq} = 100\text{ mA}$

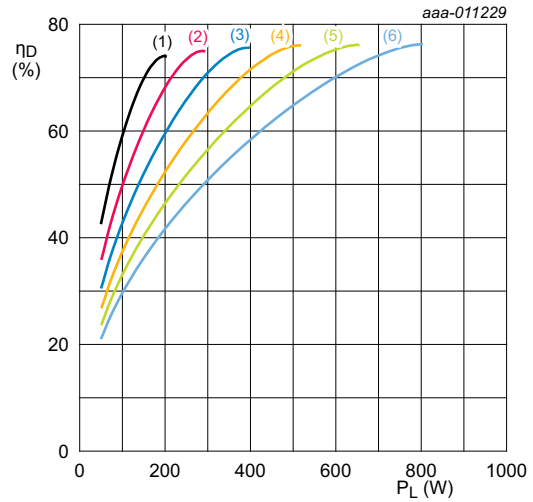
Fig 9. Drain efficiency as a function of output power; typical values



$I_{Dq} = 100\text{ mA}$; $f = 108\text{ MHz}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\text{ }\%$.

- (1) $V_{DS} = 25\text{ V}$
- (2) $V_{DS} = 30\text{ V}$
- (3) $V_{DS} = 35\text{ V}$
- (4) $V_{DS} = 40\text{ V}$
- (5) $V_{DS} = 45\text{ V}$
- (6) $V_{DS} = 50\text{ V}$

Fig 10. Power gain as a function of output power; typical values



$I_{Dq} = 100\text{ mA}$; $f = 108\text{ MHz}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 20\text{ }\%$.

- (1) $V_{DS} = 25\text{ V}$
- (2) $V_{DS} = 30\text{ V}$
- (3) $V_{DS} = 35\text{ V}$
- (4) $V_{DS} = 40\text{ V}$
- (5) $V_{DS} = 45\text{ V}$
- (6) $V_{DS} = 50\text{ V}$

Fig 11. Drain efficiency as a function of output power; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 4 leads

SOT1214A

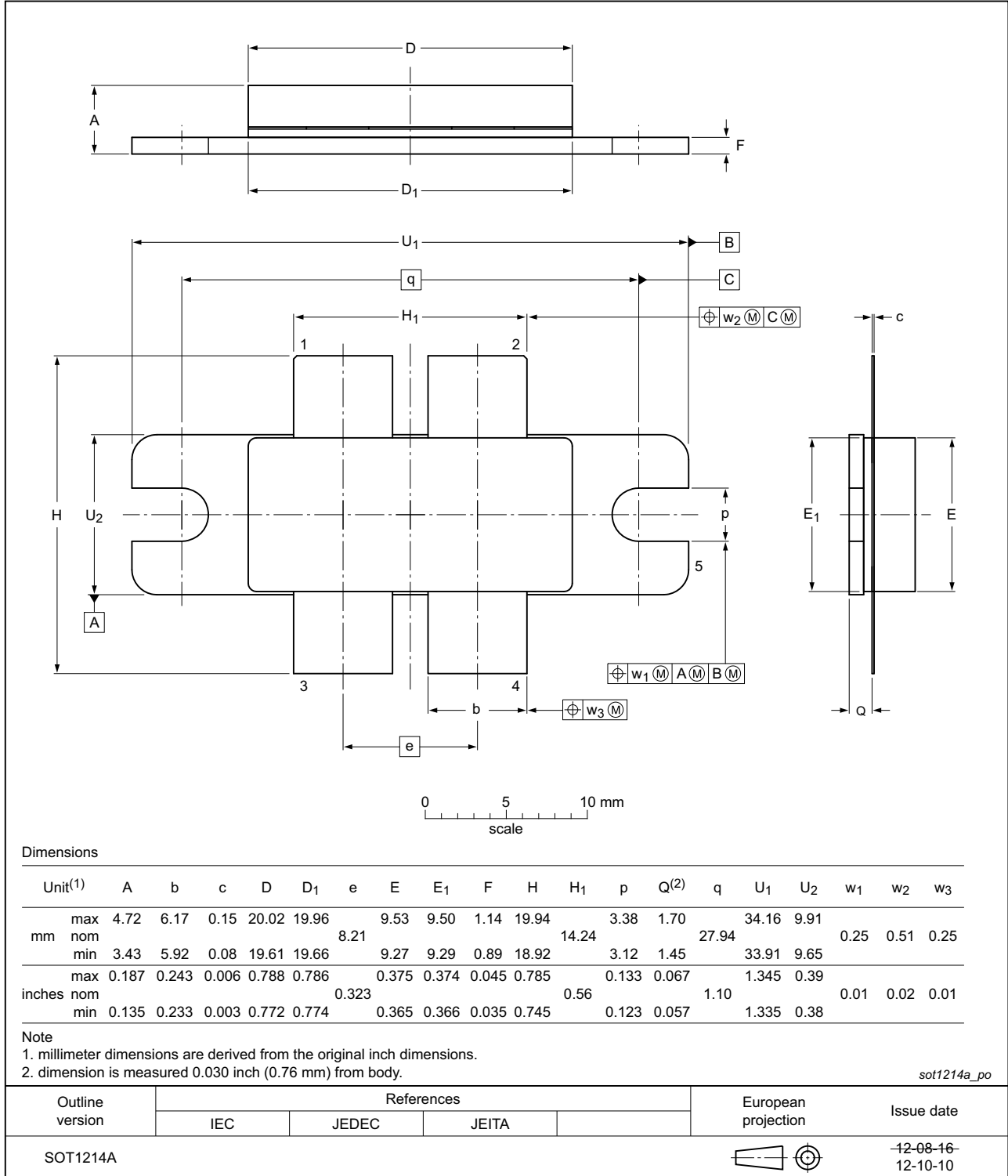


Fig 12. Package outline SOT1214A

Earless flanged ceramic package; 4 leads

SOT1214B

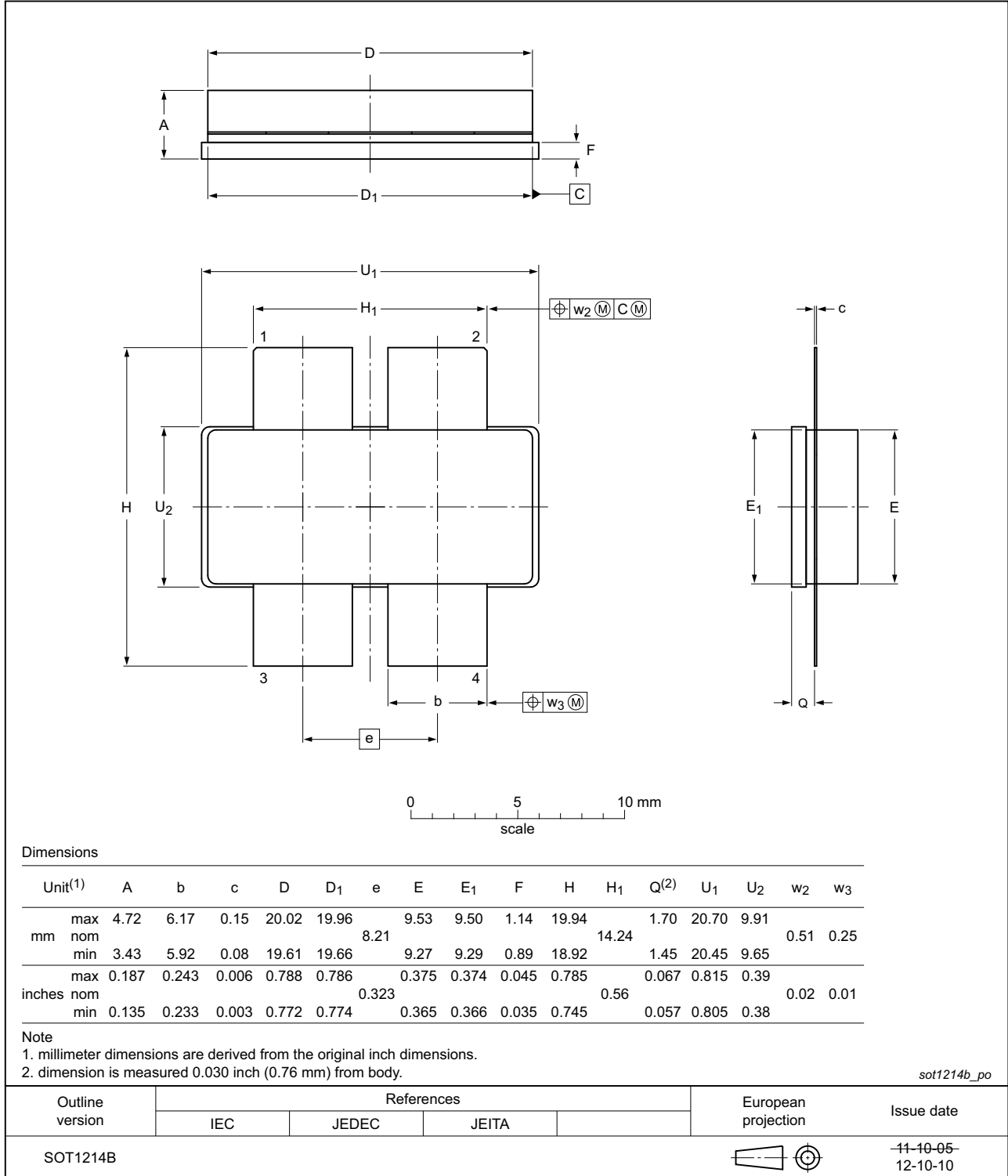


Fig 13. Package outline SOT1214B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF184XR_BLF184XRS v.3	20140401	Product data sheet	-	BLF184XR_BLF184XRS v.2
Modifications	<ul style="list-style-type: none"> The status of this document has been changed to Product data sheet Table 2 on page 2: simplified outline SOT1214B updated 			
BLF184XR_BLF184XRS v.2	20140227	Preliminary data sheet	-	BLF184XR_BLF184XRS v.1
BLF184XR_BLF184XRS v.1	20130506	Objective data sheet	-	-

12. Legal information

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Document status ^{[1][2]}	Product status ^[3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1 Product profile 1

1.1 General description 1

1.2 Features and benefits 1

1.3 Applications 1

2 Pinning information 2

3 Ordering information 2

4 Limiting values 2

5 Thermal characteristics 3

6 Characteristics 3

7 Test information 5

7.1 Ruggedness in class-AB operation 5

7.2 Impedance information 5

7.3 UIS avalanche energy 5

7.4 Test circuit 6

7.5 Graphical data 8

7.5.1 1-Tone CW pulsed 8

8 Package outline 10

9 Handling information 12

10 Abbreviations 12

11 Revision history 12

12 Legal information 13

12.1 Data sheet status 13

12.2 Definitions 13

12.3 Disclaimers 13

12.4 Trademarks 14

13 Contact information 14

14 Contents 15

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